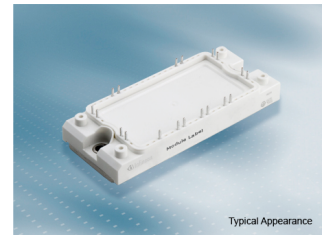


EconoPACK™2 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 50\text{ A} / I_{CRM} = 100\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Low $V_{CE,sat}$
 - Overload operation up to 175°C
- Mechanical features
 - High power and thermal cycling capability
 - Integrated NTC temperature sensor
 - Copper base plate
 - Al_2O_3 substrate with low thermal resistance
 - Solder contact technology
 - Standard housing



Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

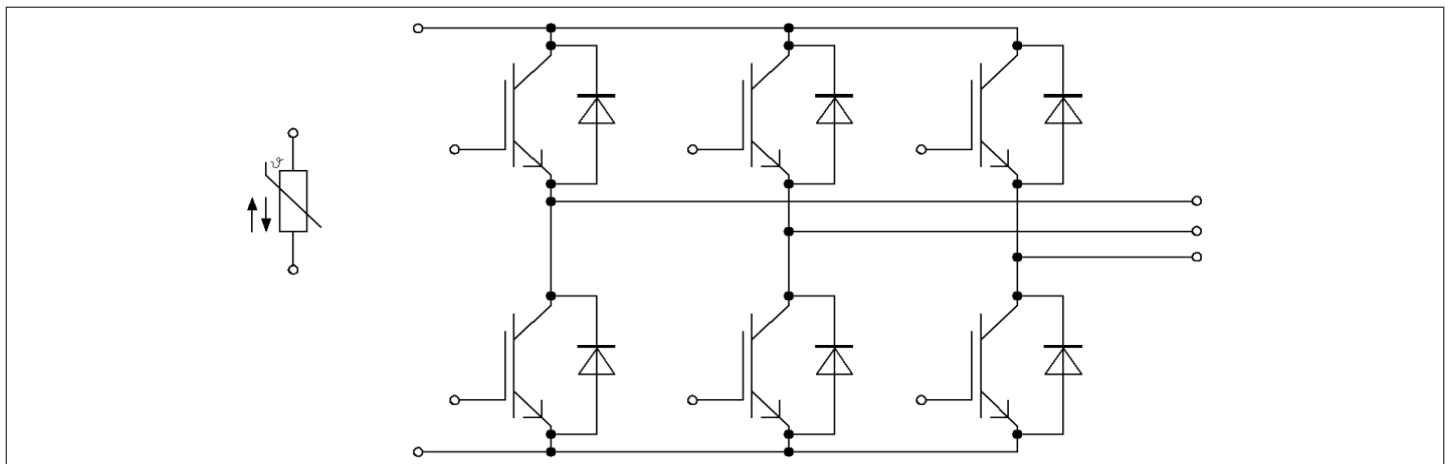


Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	NTC-Thermistor	6
5	Characteristics diagrams	7
6	Circuit diagram	12
7	Package outlines	13
8	Module label code	14
	Revision history	15
	Disclaimer	16

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		>200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			17		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		3.3		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	G			180		g

Note: The current under continuous operation is limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 115^\circ\text{C}$	50	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	100	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 50\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.50	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.64		
			$T_{vj} = 175\ ^\circ C$		1.72		
Gate threshold voltage	V_{GEth}	$I_C = 1.28\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			0.92		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			11.1		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.039		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.01	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 50\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.065		μs
			$T_{vj} = 125\ ^\circ C$		0.067		
			$T_{vj} = 175\ ^\circ C$		0.068		
Rise time (inductive load)	t_r	$I_C = 50\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.041		μs
			$T_{vj} = 125\ ^\circ C$		0.045		
			$T_{vj} = 175\ ^\circ C$		0.047		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.260		μs
			$T_{vj} = 125\ ^\circ C$		0.340		
			$T_{vj} = 175\ ^\circ C$		0.380		
Fall time (inductive load)	t_f	$I_C = 50\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.110		μs
			$T_{vj} = 125\ ^\circ C$		0.210		
			$T_{vj} = 175\ ^\circ C$		0.270		
Turn-on energy loss per pulse	E_{on}	$I_C = 50\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega, di/dt = 885\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		4.89		mJ
			$T_{vj} = 125\ ^\circ C$		6.3		
			$T_{vj} = 175\ ^\circ C$		7.34		
Turn-off energy loss per pulse	E_{off}	$I_C = 50\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega, dv/dt = 3000\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		3.19		mJ
			$T_{vj} = 125\ ^\circ C$		5.15		
			$T_{vj} = 175\ ^\circ C$		6.33		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_P \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$		190		A
			$t_P \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$		180		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.579	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		0.147		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC forward current	I_F			50	A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$		100	A
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	465	A^2s
			$T_{vj} = 175^\circ\text{C}$	420	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$	1.72	2.10	V
			$T_{vj} = 125^\circ\text{C}$	1.59		
			$T_{vj} = 175^\circ\text{C}$	1.52		
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 50 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 885 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	25		A
			$T_{vj} = 125^\circ\text{C}$	33		
			$T_{vj} = 175^\circ\text{C}$	38		
Recovered charge	Q_r	$V_R = 600 \text{ V}, I_F = 50 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 885 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$	3.23		μC
			$T_{vj} = 125^\circ\text{C}$	6.46		
			$T_{vj} = 175^\circ\text{C}$	8.88		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 600 \text{ V}$, $I_F = 50 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 885 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	1.02		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2.21		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	3.16		
Thermal resistance, junction to case	R_{thJC}	per diode			0.900	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}^*\text{K})$		0.168		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ }^\circ\text{C}$, $R_{100} = 493 \text{ } \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

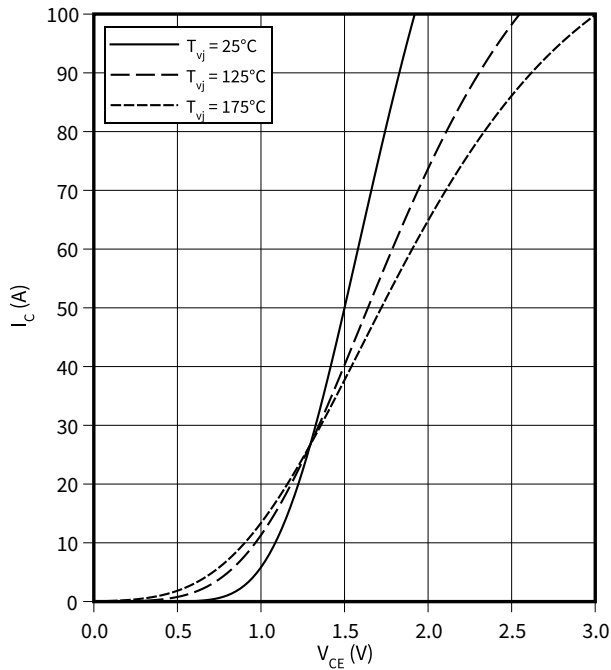
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

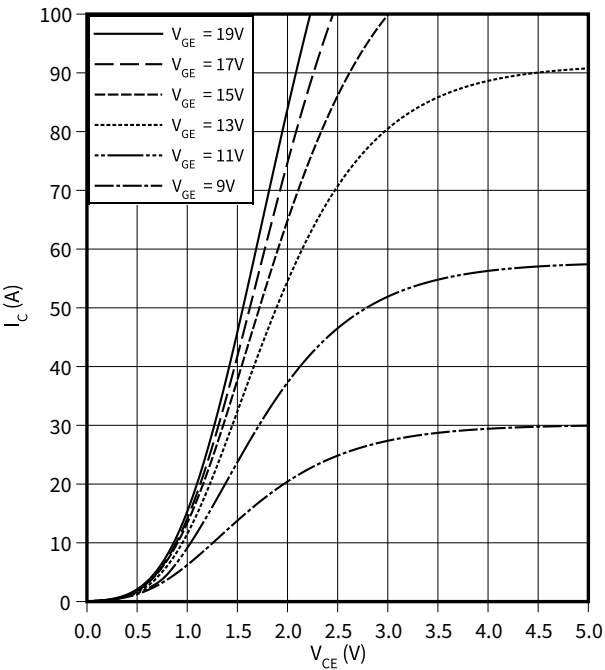
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

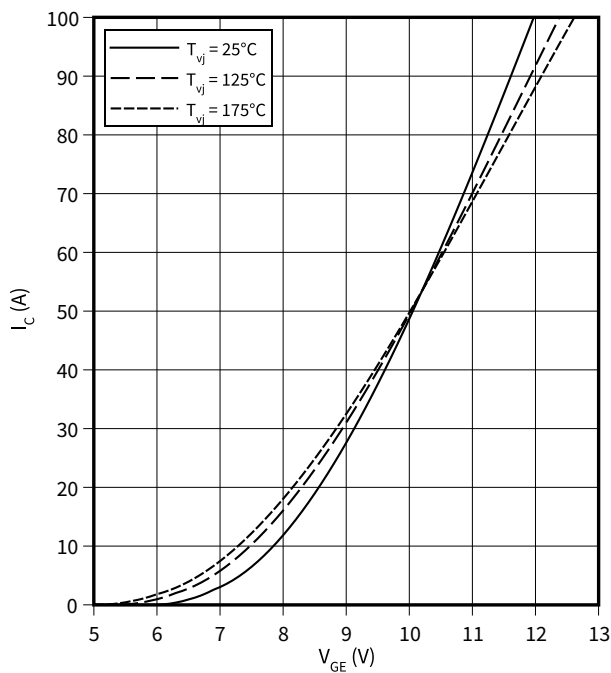
$T_{vj} = 175^\circ\text{C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

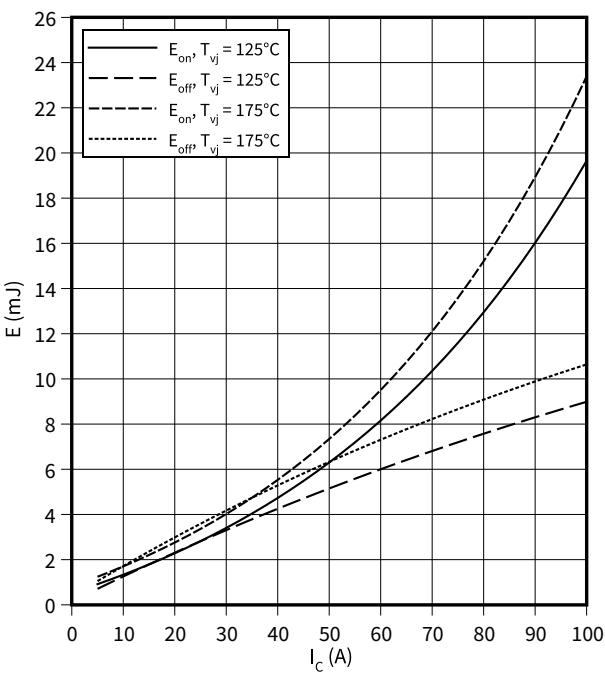
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

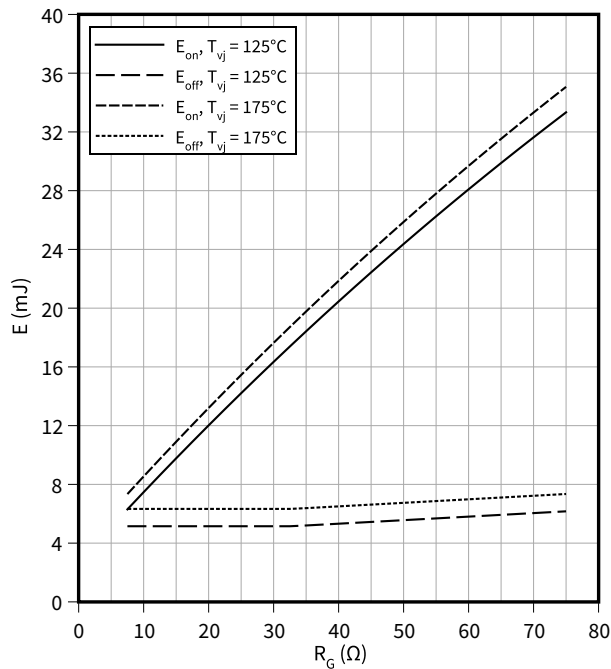
$R_{Goff} = 7.5\ \Omega$, $R_{Gon} = 7.5\ \Omega$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$



5 Characteristics diagrams

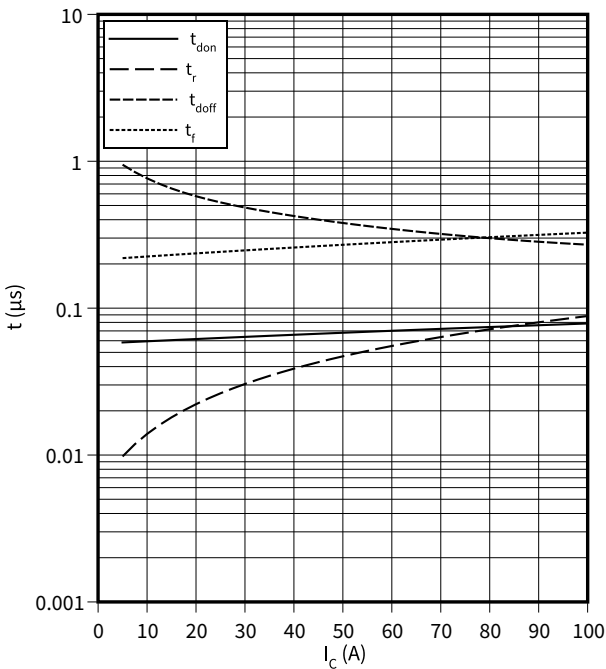
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $I_C = 50\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$



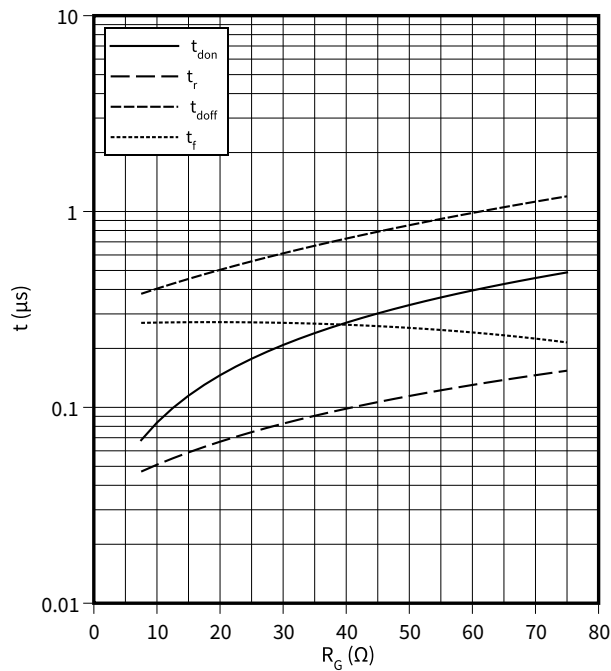
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 7.5\text{ }\Omega$, $R_{Gon} = 7.5\text{ }\Omega$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



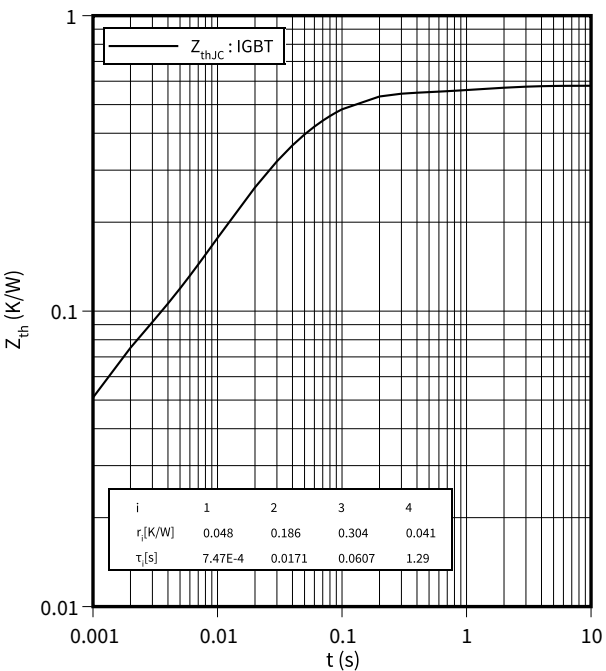
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $I_C = 50\text{ A}$, $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$



Transient thermal impedance , IGBT, Inverter

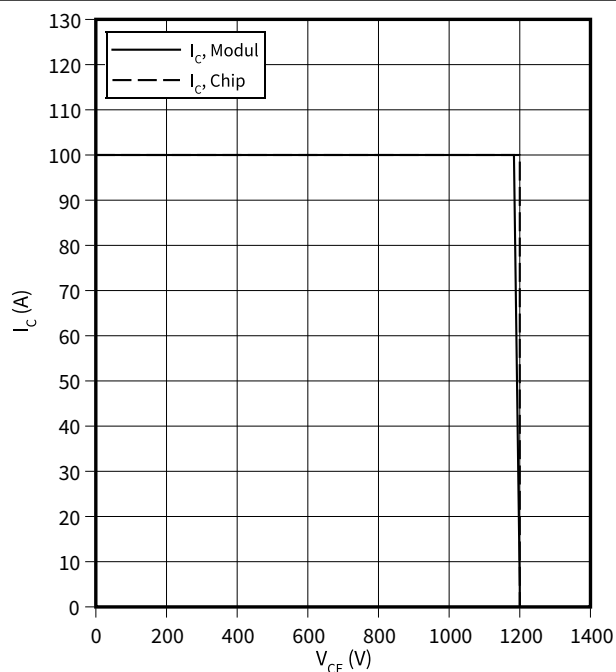
$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$$I_C = f(V_{CE})$$

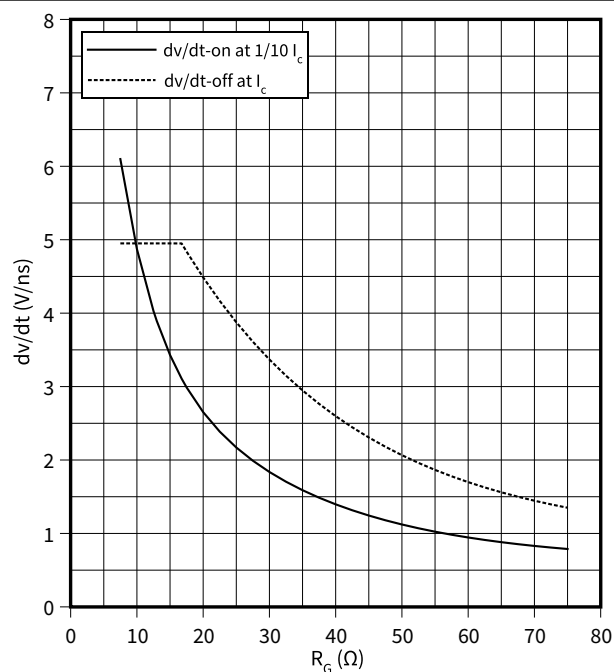
$$R_{Goff} = 7.5 \, \Omega, V_{GE} = \pm 15 \, V, T_{vj} = 175 \, ^\circ C$$



Voltage slope (typical), IGBT, Inverter

$$dv/dt = f(R_G)$$

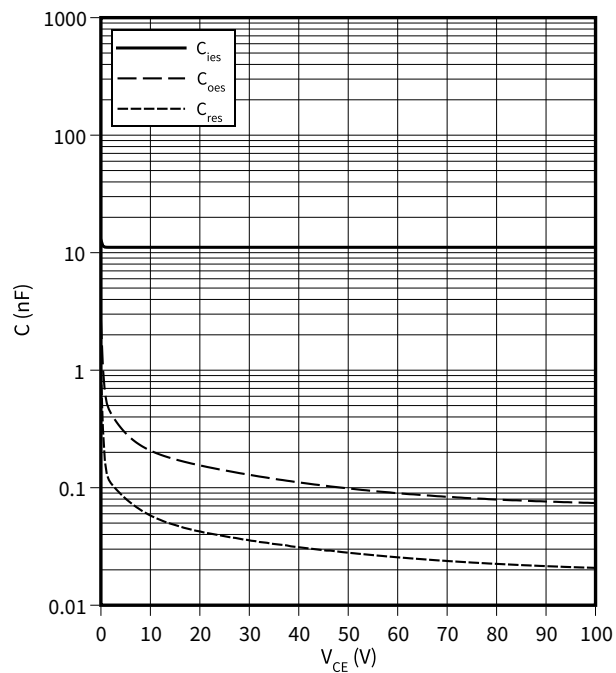
$$I_C = 50 \, A, V_{CE} = 600 \, V, V_{GE} = \pm 15 \, V, T_{vj} = 25 \, ^\circ C$$



Capacity characteristic (typical), IGBT, Inverter

$$C = f(V_{CE})$$

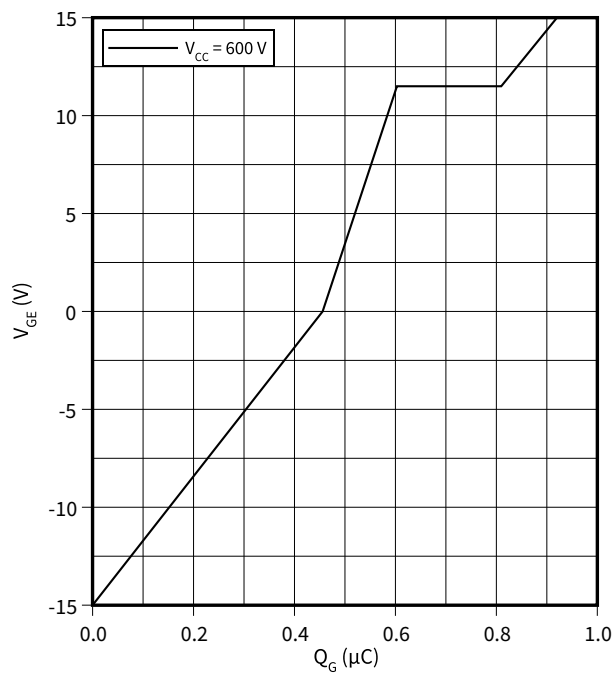
$$f = 100 \, kHz, V_{GE} = 0 \, V, T_{vj} = 25 \, ^\circ C$$



Gate charge characteristic (typical), IGBT, Inverter

$$V_{GE} = f(Q_G)$$

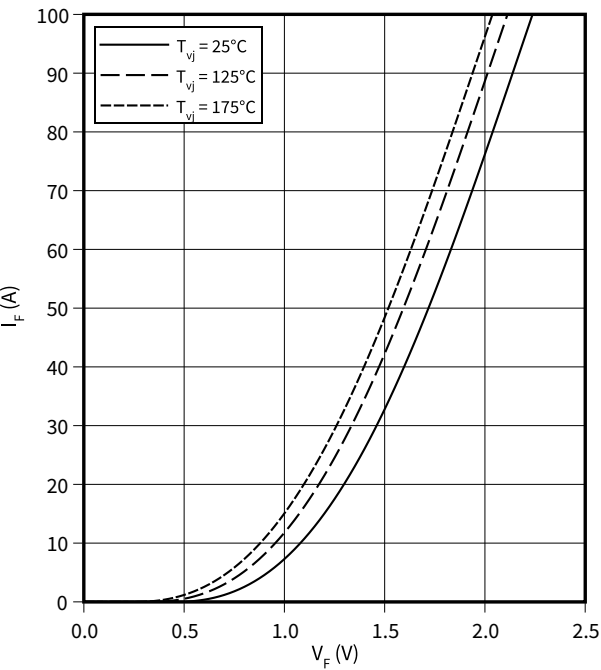
$$I_C = 50 \, A, T_{vj} = 25 \, ^\circ C$$



5 Characteristics diagrams

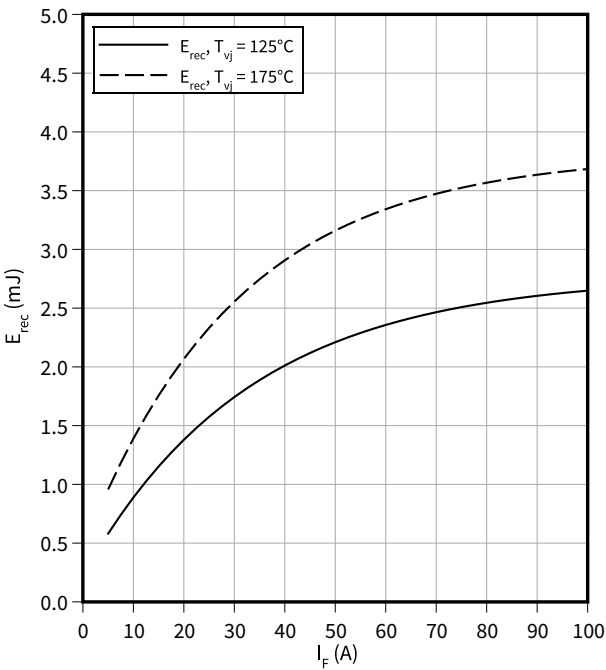
Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$



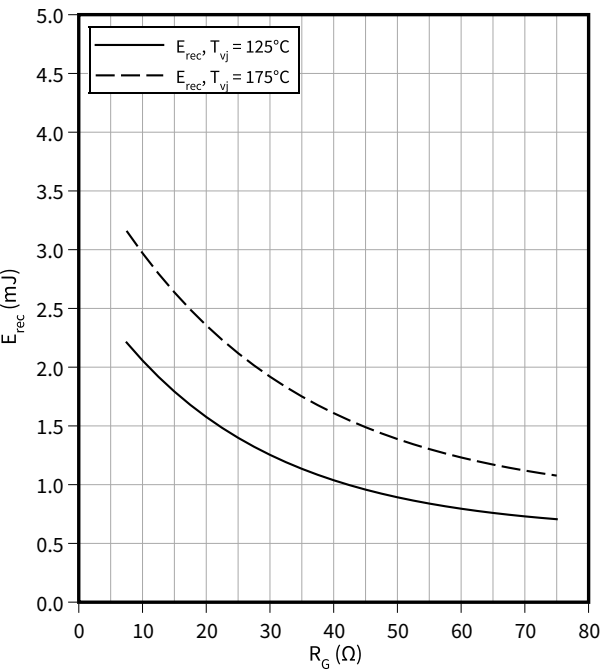
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = 7.5\ \Omega, V_R = 600\ \text{V}$



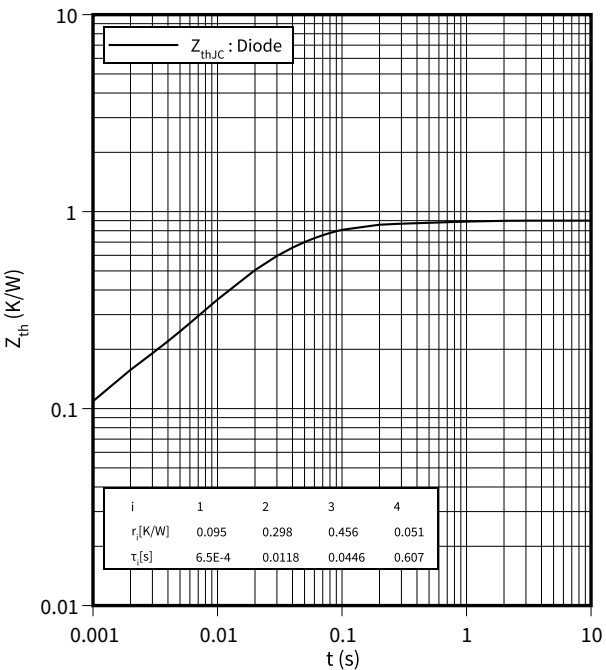
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 50\ \text{A}, V_R = 600\ \text{V}$



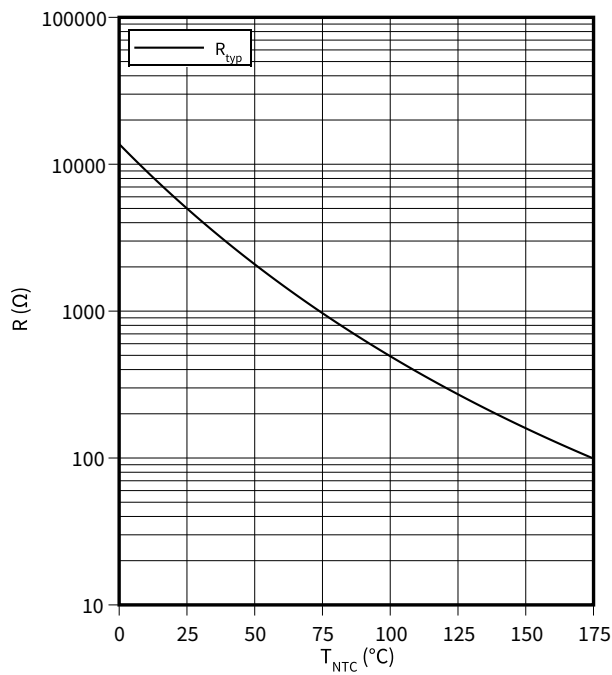
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

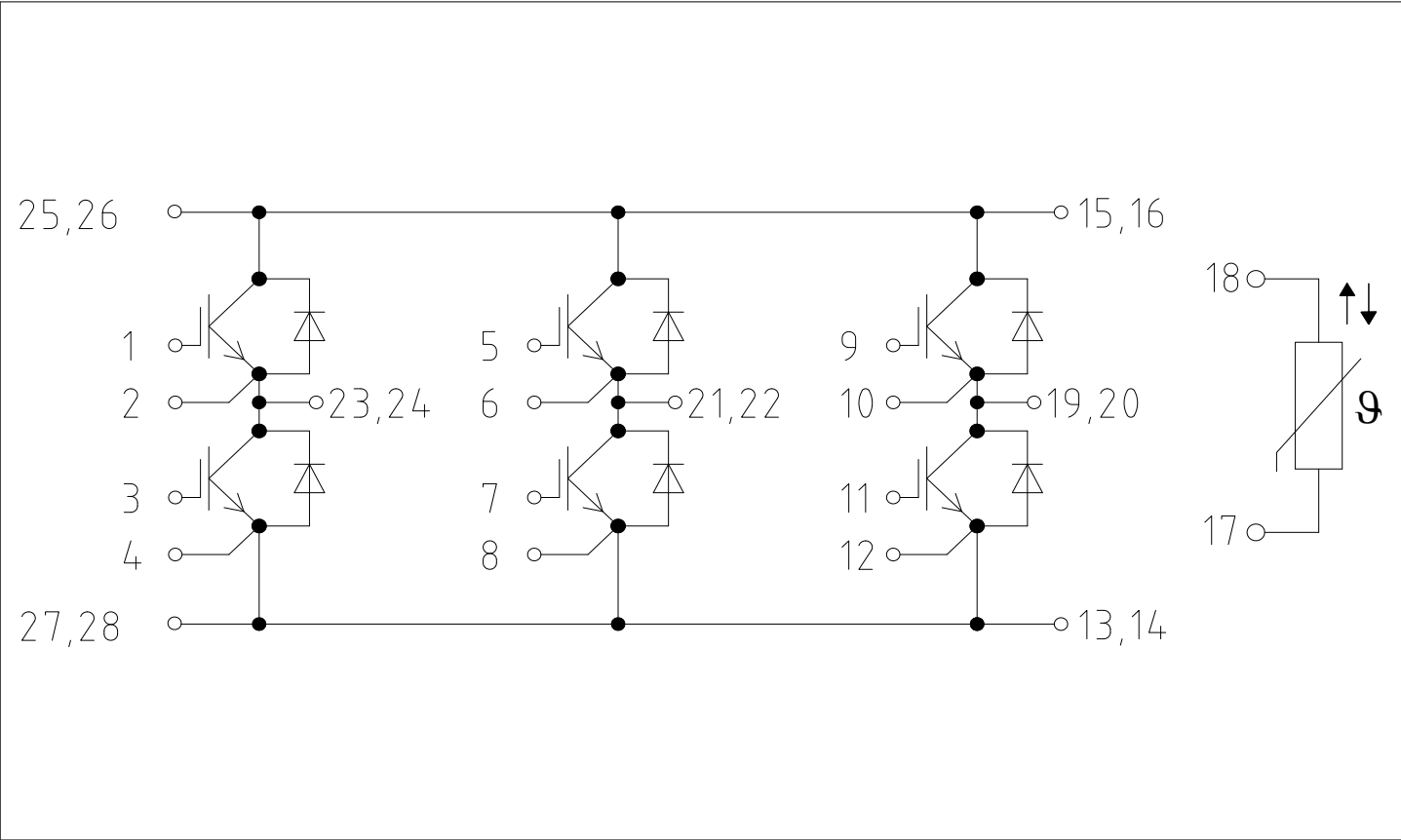


Figure 1



8 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	Content	Digit	Example
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	 71549142846550549911530  71549142846550549911530		

Figure 3

Revision history

Document revision	Date of release	Description of changes
1.00	2021-12-16	Final datasheet

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